



PJM150N30TO

N-Channel Enhancement Mode Power MOSFET

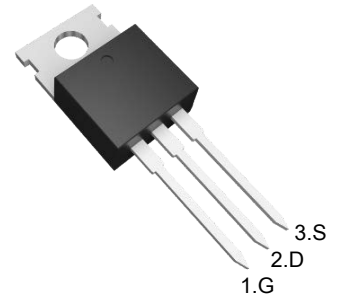
Features

- Excellent package for good heat dissipation
- Fully characterized avalanche voltage and current
- High density cell design for ultra low $R_{DS(on)}$
- $V_{DS} = 30V, I_D = 150A$
 $R_{DS(on)} < 3m\Omega @ V_{GS} = 10V$

Applications

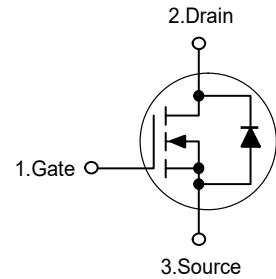
- Power switching application
- Hard switched and high frequency circuits
- Uninterruptible power supply

TO-220



1.Gate 2.Drain 3.Source

Schematic diagram



Absolute Maximum Ratings

Ratings at 25°C ambient temperature unless otherwise specified.

Parameter	Symbol	Value	Unit
Drain-Source Voltage	V_{DS}	30	V
Gate-Source Voltage	V_{GS}	± 20	V
Drain Current-Continuous	I_D	150	A
Drain Current-Pulsed ^{Note1}	I_{DM}	600	A
Single Pulse Avalanche Energy ^{Note4}	E_{AS}	1800	mJ
Maximum Power Dissipation	P_D	130	W
Junction Temperature	T_J	175	°C
Storage Temperature Range	T_{STG}	-55 to +175	°C

Thermal Characteristics

Maximum Junction-to-Case ^{Note2}	$R_{\theta JC}$	1.15	°C/W
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Electrical Characteristics

(Ta=25°C unless otherwise specified)

Parameter	Symbol	Test Condition	Min.	Typ.	Max.	Unit
Static Characteristics						
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS}=0V, I_D=250\mu A$	30	--	--	V
Drain-Source Leakage Current	I_{DSS}	$V_{DS}=30V, V_{GS}=0V$	--	--	1.0	μA
Gate-Body Leakage Current	I_{GSS}	$V_{GS}=\pm 20V, V_{DS}=0V$	--	--	± 0.1	μA
Gate Threshold Voltage ^{Note3}	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=250\mu A$	1.0	1.6	3.0	V
Drain-Source On-Resistance ^{Note3}	$R_{DS(on)}$	$V_{GS}=10V, I_D=25A$	--	2.25	3.0	m Ω
Forward Transconductance ^{Note3}	g_{FS}	$V_{DS}=5V, I_D=25A$	30	--	--	S
Dynamic Characteristics						
Input Capacitance	C_{iss}	$V_{DS}=15V, V_{GS}=0V, f=1MHz$	--	5000	--	pF
Output Capacitance	C_{oss}		--	1150	--	pF
Reverse Transfer Capacitance	C_{rss}		--	580	--	pF
Switching Characteristics						
Turn-on Delay Time	$t_{d(on)}$	$V_{DD}=15V, V_{GS}=10V$ $I_D=25A, R_G=1.8\Omega$	--	26	--	nS
Turn-on Rise Time	t_r		--	24	--	nS
Turn-off Delay Time	$t_{d(off)}$		--	95	--	nS
Turn-off Fall Time	t_f		--	40	--	nS
Total Gate Charge	Q_g	$V_{DD}=15V, V_{GS}=10V, I_D=25A$	--	35	--	nC
Gate-Source Charge	Q_{gs}		--	8	--	nC
Gate-Drain Charge	Q_{gd}		--	13	--	nC
Source-Drain Diode Characteristics						
Diode Forward Voltage ^{Note3}	V_{SD}	$V_{GS}=0V, I_S=150A$	--	--	1.2	V
Diode Forward Current ^{Note2}	I_S		--	--	150	A

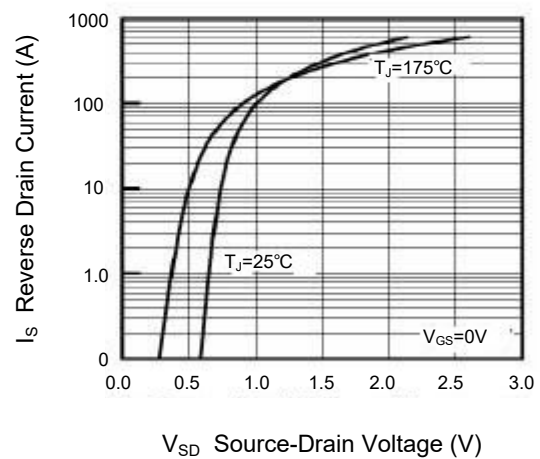
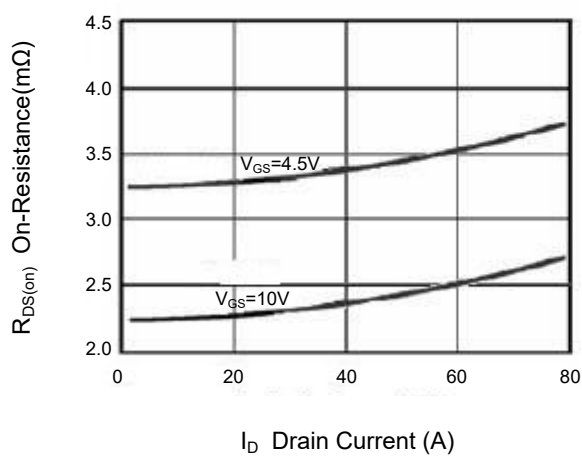
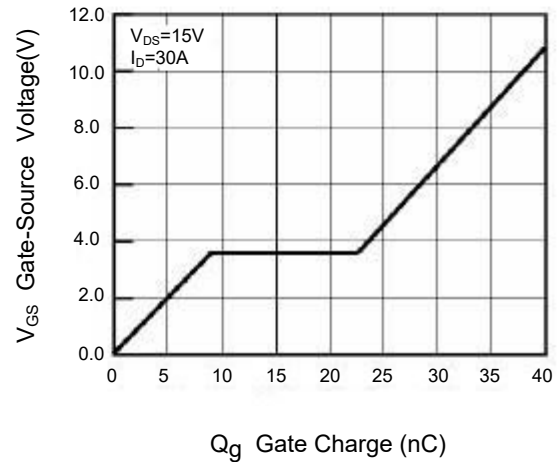
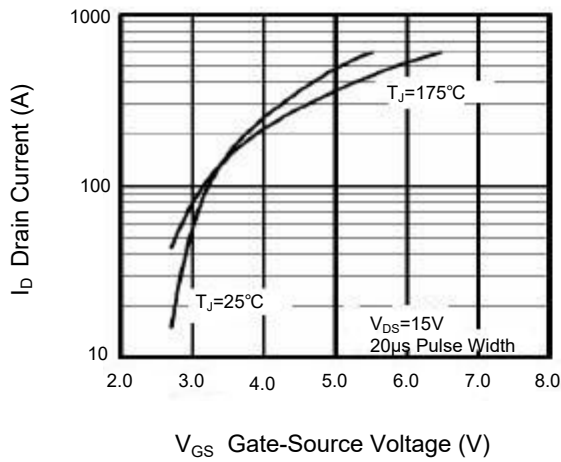
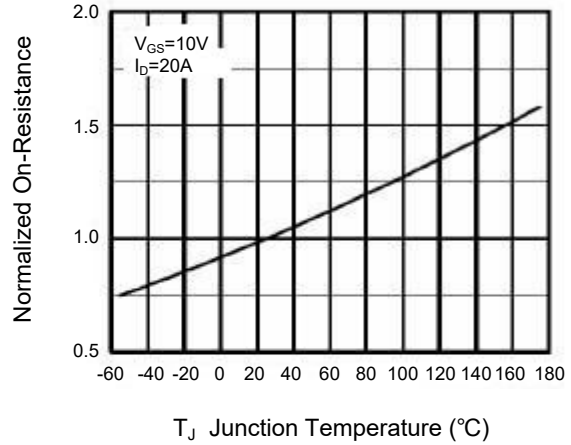
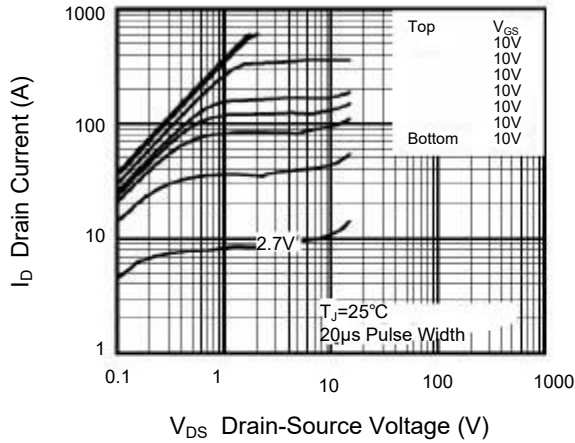
- Note: 1. Repetitive Rating: Pulse width limited by maximum junction temperature.
 2. Surface Mounted on FR4 Board, $t \leq 10$ sec.
 3. Pulse Test: Pulse width $\leq 300\mu s$, duty cycle $\leq 2\%$
 4. E_{AS} Condition: $T_j=25^\circ C, V_{DD}=15V, V_{GS}=10V, L=1.0mH, R_G=25\Omega$



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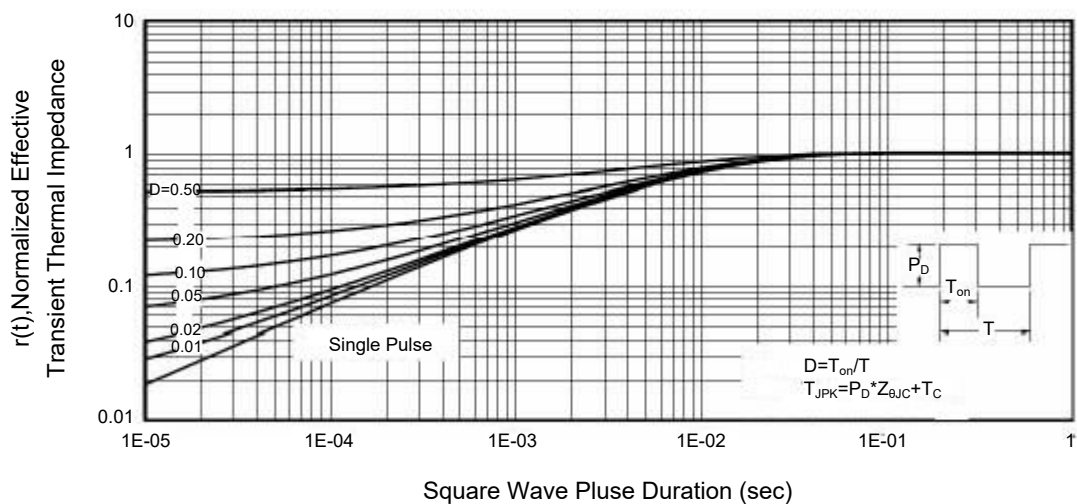
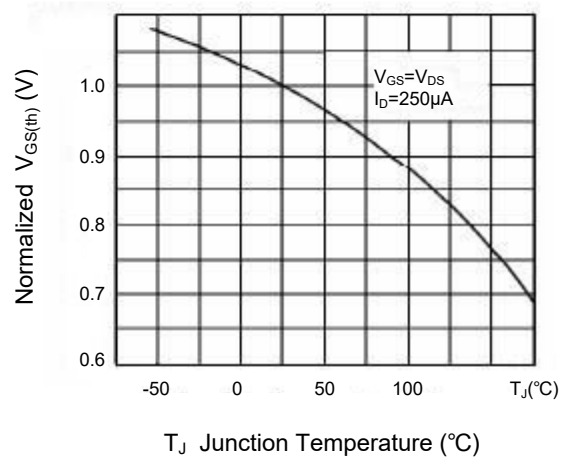
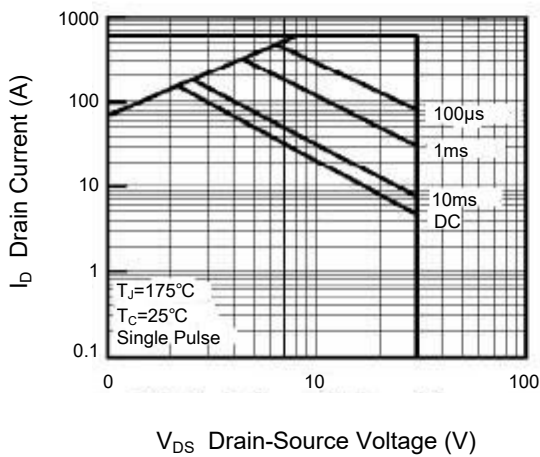
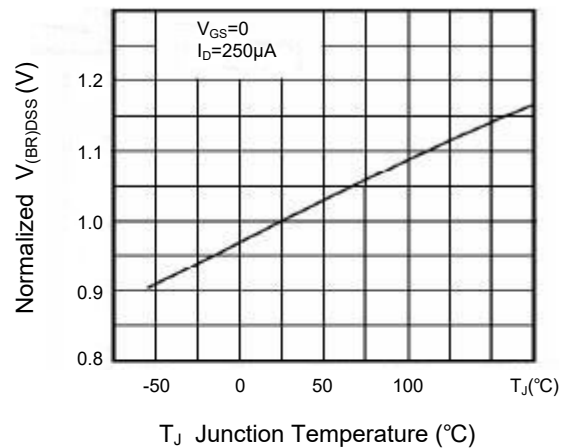
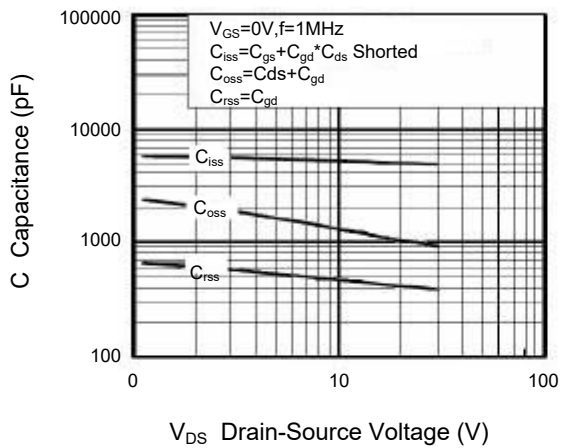
Typical Characteristic Curves

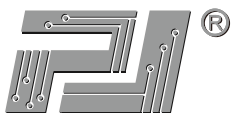




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Package Outline

TO-220

Dimensions in mm

